

MPS6729

Preferred Device

One Watt Amplifier Transistor

PNP Silicon

Features

- Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-80	Vdc
Collector-Base Voltage	V_{CBO}	-80	Vdc
Emitter-Base Voltage	V_{EBO}	-4.0	Vdc
Collector Current - Continuous	I_C	-500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	W mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5 20	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

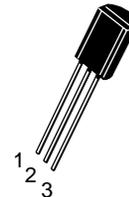
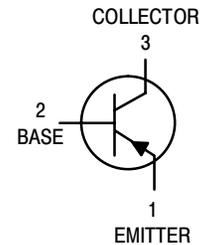
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	$^\circ\text{C}/\text{W}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



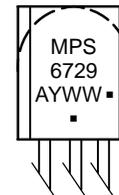
ON Semiconductor®

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TO-92 (TO-226)
CASE 29-10
STYLE 1

MARKING DIAGRAM



MPS6729 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
MPS6729	TO-92	5000 Units / Bulk
MPS6729G	TO-92 (Pb-Free)	5000 Units / Bulk

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

MPS6729

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 1) ($I_C = -1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	-80	-	Vdc
Collector–Base Breakdown Voltage ($I_C = 0.1\text{ mA}$, $I_E = 0$)	$V_{(BR)CBO}$	-80	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ($V_{CB} = -60\text{ Vdc}$, $I_E = 0$)	I_{CBO}	-	-0.1	μA dc
Emitter Cutoff Current ($V_{EB} = -5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	-10	μA dc
ON CHARACTERISTICS (Note 1)				
DC Current Gain ($I_C = -50\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -250\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)	h_{FE}	80 50	- 250	-
Collector–Emitter Saturation Voltage ($I_C = -250\text{ mA}$, $I_B = -10\text{ mA}$)	$V_{CE(sat)}$	-	-0.5	Vdc
Base–Emitter On Voltage ($I_C = -250\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)	$V_{BE(on)}$	-	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Collector–Base Capacitance ($V_{CB} = -10\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{cb}	-	30	pF
Small–Signal Current Gain ($I_C = 200\text{ mA}$, $V_{CE} = 5.0\text{ V}$, $f = 20\text{ MHz}$)	h_{fe}	2.5	25	

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

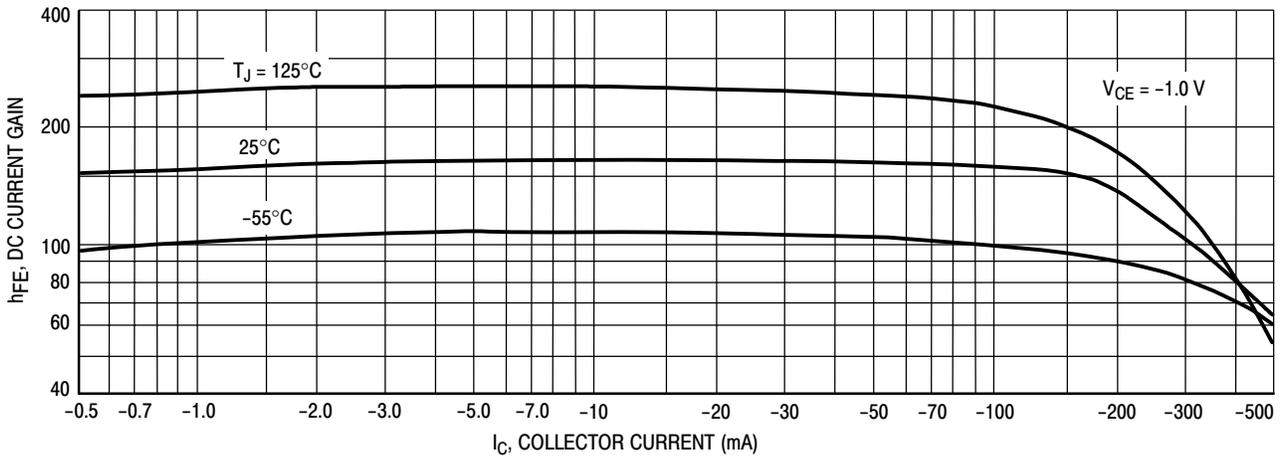


Figure 1. DC Current Gain

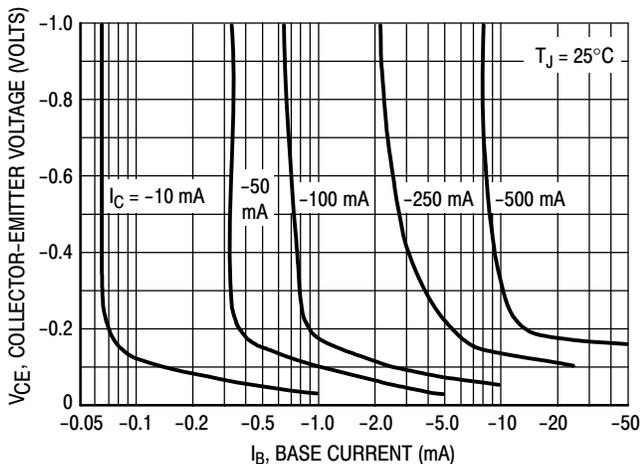


Figure 2. Collector Saturation Region

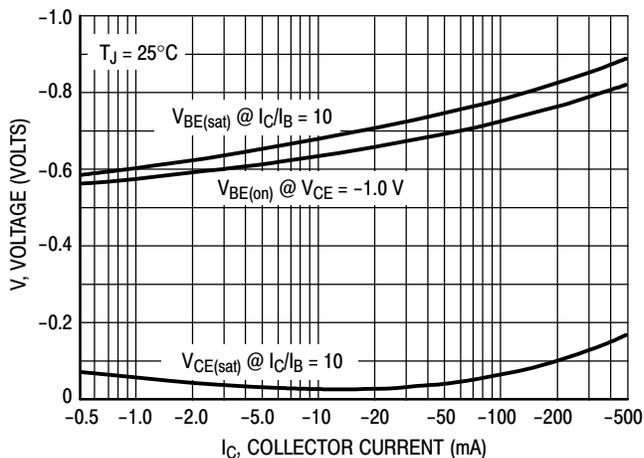


Figure 3. "On" Voltages

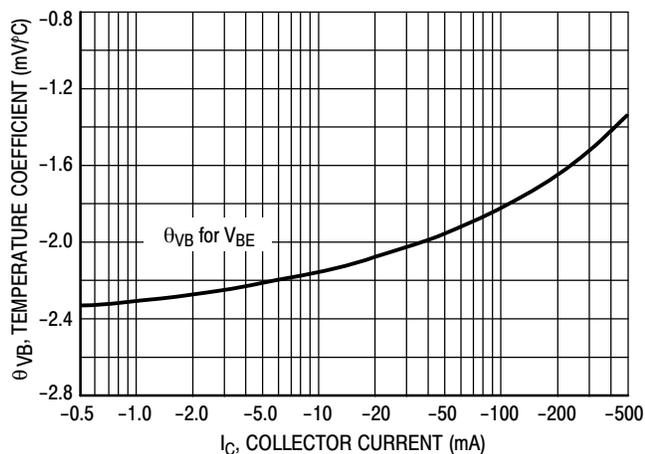


Figure 4. Base-Emitter Temperature Coefficient

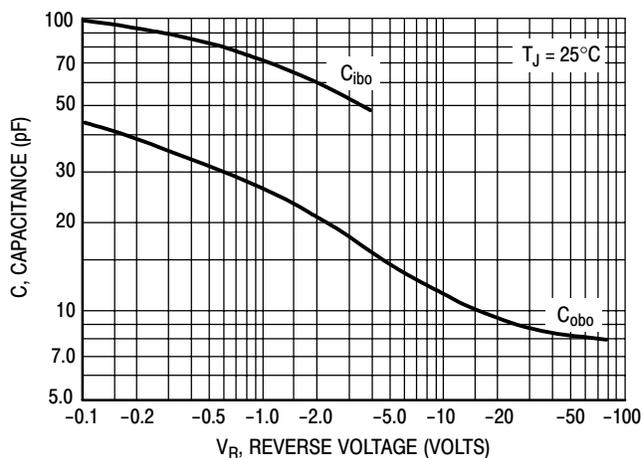


Figure 5. Capacitance

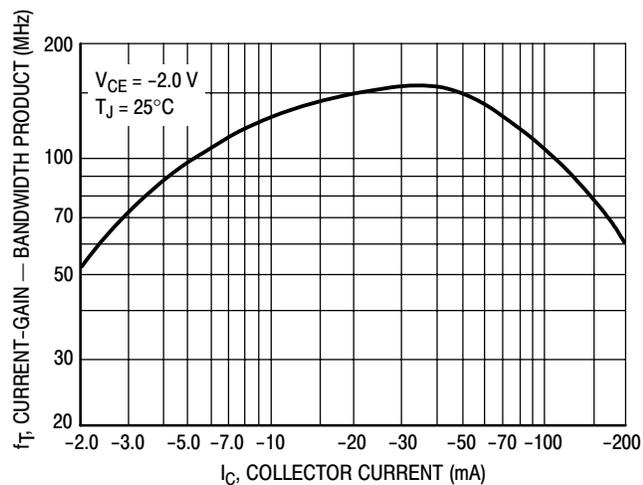


Figure 6. Current-Gain - Bandwidth Product

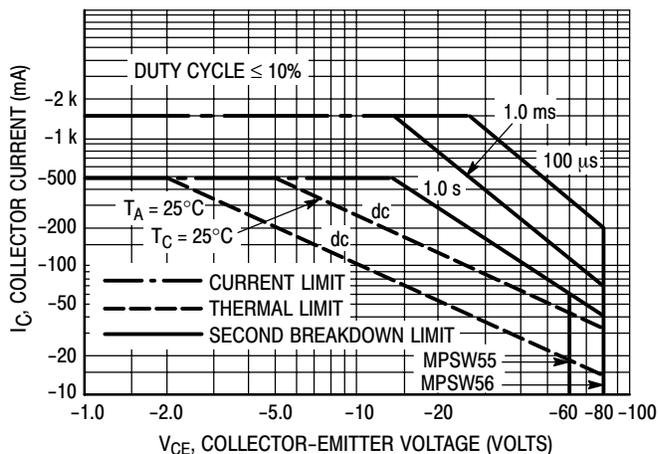
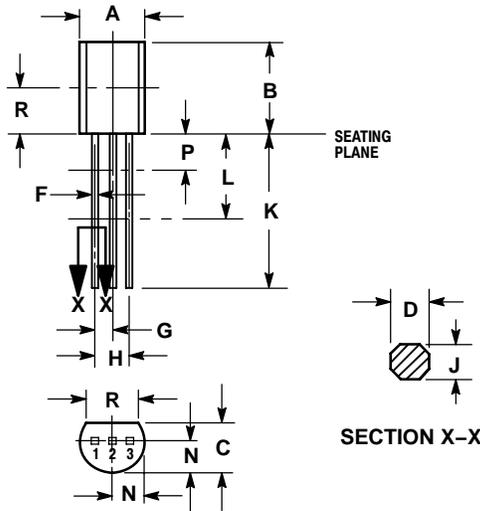


Figure 7. Active Region - Safe Operating Area

MPS6729

PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-10
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---

STYLE 1:

- PIN 1. EMITTER
- BASE
- COLLECTOR

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